Designer's™ Data Sheet

Insulated Gate Bipolar Transistor

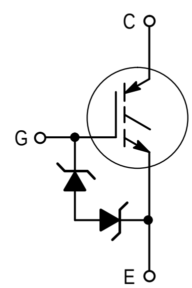
N–Channel Enhancement–Mode Silicon Gate

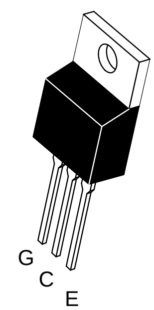
MGP15N60U

IGBT IN TO–220
15 A @ 90°C
26 A @ 25°C
600 VOLTS
VERY LOW ON–VOLTAGE

This Insulated Gate Bipolar Transistor (IGBT) uses an advanced termination scheme to provide an enhanced and reliable high voltage–blocking capability. It also provides low on–voltage which results in efficient operation at high current.

- Industry Standard TO–220 Package
- High Speed E_{off}: 63 μJ/A typical at 125°C
- Low On–Voltage – 1.7 V typical at 8.0 A, 125°C
- Robust High Voltage Termination
- ESD Protection Gate–Emitter Zener Diodes





CASE 221A–09
STYLE 9
TO–220AB

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CES}	600	Vdc
Collector–Gate Voltage (R_{GE} = 1.0 MΩ)	V_{CGR}	600	Vdc
Gate–Emitter Voltage — Continuous	V_{GE}	±20	Vdc
Collector Current — Continuous @ T_C = 25°C — Continuous @ T_C = 90°C — Repetitive Pulsed Current (1)	I_{C25} I_{C90} I_{CM}	26 15 52	Adc Apk
Total Power Dissipation @ T_C = 25°C Derate above 25°C	P_D	96 0.77	Watts W/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–55 to 150	°C
Thermal Resistance — Junction to Case – IGBT — Junction to Ambient	$R_{\theta JC}$ $R_{\theta JA}$	1.3 65	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8″ from case for 5 seconds	T_L	260	°C
Mounting Torque, 6–32 or M3 screw		10 lbf•in (1.13 N•m)	

(1) Pulse width is limited by maximum junction temperature. Repetitive rating.

Designer's Data for "Worst Case" Conditions — The Designer's Data Sheet permits the design of most circuits entirely from the information presented. SOA Limit curves — representing boundaries on device characteristics — are given to facilitate "worst case" design.

REV 1

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector–to–Emitter Breakdown Voltage (V_{GE} = 0 Vdc, I_C = 25 μAdc)		$V_{(BR)CES}$	600	—	—	Vdc
Temperature Coefficient (Positive)			—	870	—	mV/°C
Emitter–to–Collector Breakdown Voltage (V_{GE} = 0 Vdc, I_{EC} = 100 mAdc)		$V_{(BR)ECS}$	15	—	—	Vdc
Zero Gate Voltage Collector Current (V_{CE} = 600 Vdc, V_{GE} = 0 Vdc)		I_{CES}	—	—	10	μAdc
(V_{CE} = 600 Vdc, V_{GE} = 0 Vdc, T_J = 125°C)			—	—	200	
Gate–Body Leakage Current (V_{GE} = ± 20 Vdc, V_{CE} = 0 Vdc)		I_{GES}	—	—	50	μAdc
ON CHARACTERISTICS (1)						
Collector–to–Emitter On–State Voltage (V_{GE} = 15 Vdc, I_C = 4.0 Adc)		$V_{CE(on)}$	—	1.4	1.7	Vdc
(V_{GE} = 15 Vdc, I_C = 4.0 Adc, T_J = 125°C)			—	1.3	—	
(V_{GE} = 15 Vdc, I_C = 8.0 Adc)			—	1.7	2.0	
Gate Threshold Voltage (V_{CE} = V_{GE}, I_C = 1.0 mAdc)		$V_{GE(th)}$	3.0	5.5	7.0	Vdc
Threshold Temperature Coefficient (Negative)			—	10	—	mV/°C
Forward Transconductance (V_{CE} = 10 Vdc, I_C = 8.0 Adc)		g_{fe}	—	7.0	—	Mhos
DYNAMIC CHARACTERISTICS						
Input Capacitance	(V_{CE} = 25 Vdc, V_{GE} = 0 Vdc, f = 1.0 MHz)	C_{ies}	—	806	—	pF
Output Capacitance		C_{oes}	—	78	—	
Transfer Capacitance		C_{res}	—	13	—	
SWITCHING CHARACTERISTICS (1)						
Turn–On Delay Time	(V_{CC} = 360 Vdc, I_C = 8.0 Adc, V_{GE} = 15 Vdc, L = 300 μH, R_G = 20 Ω) Energy losses include “tail”	$t_{d(on)}$	—	35	—	ns
Rise Time		t_r	—	34	—	
Turn–Off Delay Time		$t_{d(off)}$	—	105	—	
Fall Time		t_f	—	200	—	
Turn–Off Switching Loss		E_{off}	—	250	—	μJ
Turn–On Delay Time	(V_{CC} = 360 Vdc, I_C = 8.0 Adc, V_{GE} = 15 Vdc, L = 300 μH, R_G = 20 Ω, T_J = 125°C) Energy losses include “tail”	$t_{d(on)}$	—	36	—	ns
Rise Time		t_r	—	39	—	
Turn–Off Delay Time		$t_{d(off)}$	—	206	—	
Fall Time		t_f	—	255	—	
Turn–Off Switching Loss		E_{off}	—	510	—	μJ
Gate Charge	(V_{CC} = 360 Vdc, I_C = 8.0 Adc, V_{GE} = 15 Vdc)	Q_T	—	39.2	—	nC
		Q_1	—	8.7	—	
		Q_2	—	17.4	—	
INTERNAL PACKAGE INDUCTANCE						
Internal Emitter Inductance (Measured from the emitter lead 0.25″ from package to emitter bond pad)		L_E	—	7.5	—	nH

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.

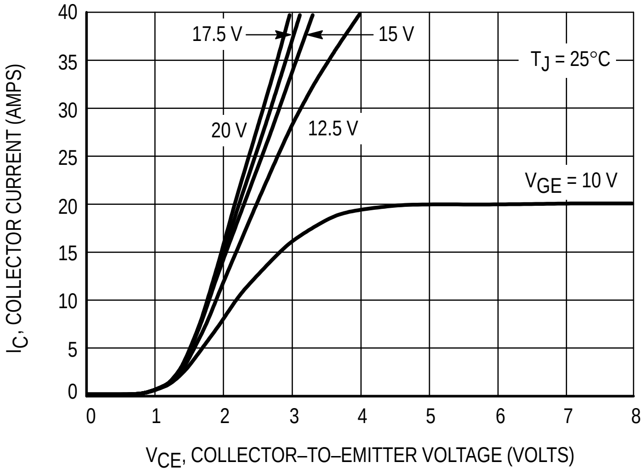


Figure 1. Output Characteristics

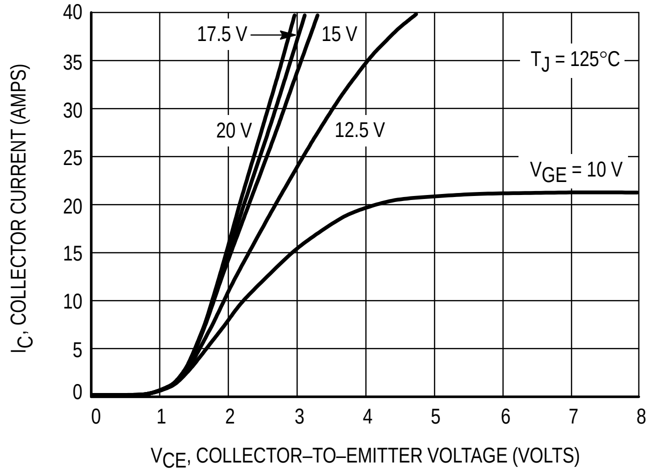


Figure 2. Output Characteristics

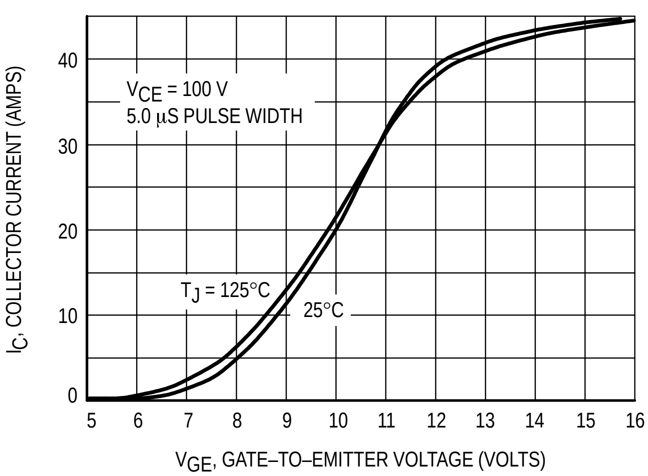


Figure 3. Transfer Characteristics

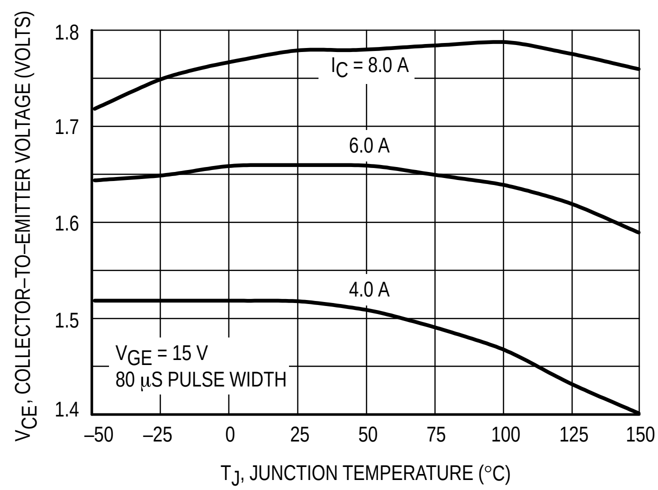


Figure 4. Collector–To–Emitter Saturation Voltage versus Junction Temperature

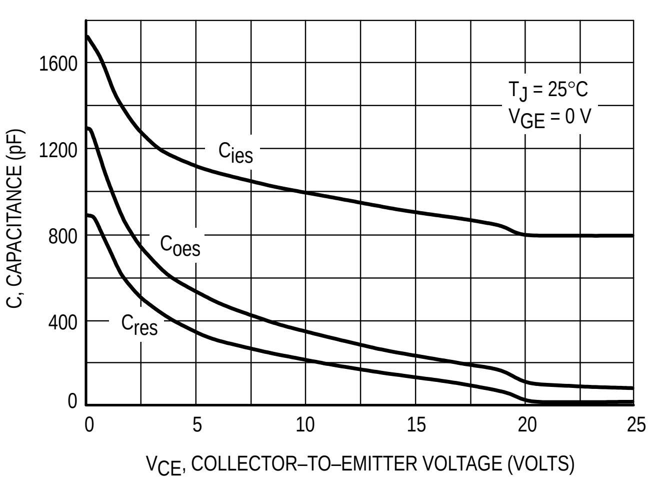


Figure 5. Capacitance Variation

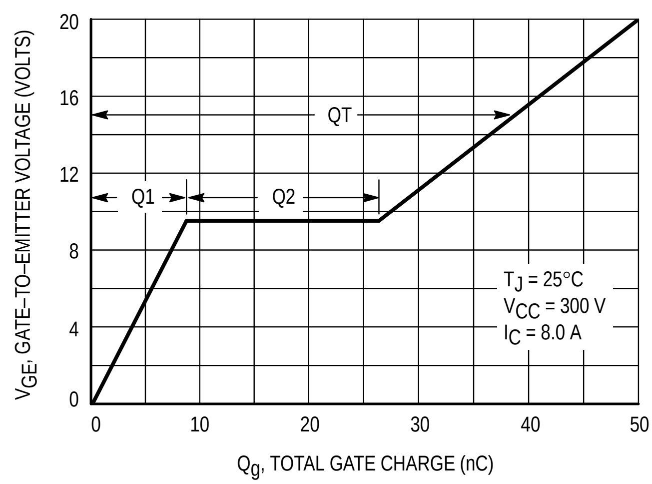


Figure 6. Gate–To–Emitter Voltage versus Total Charge

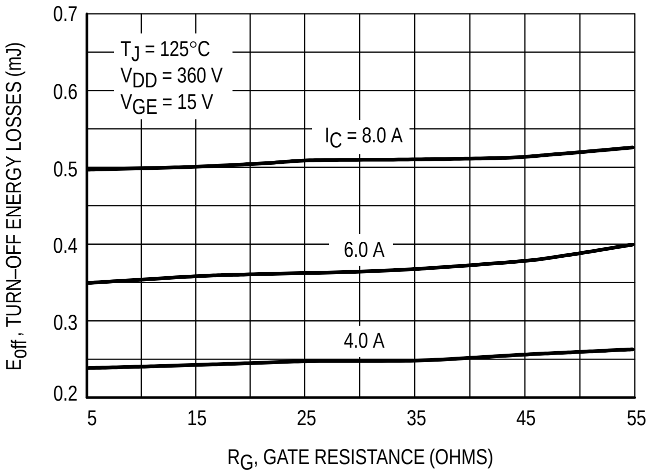


Figure 7. Turn–Off Energy Losses versus Gate Resistance

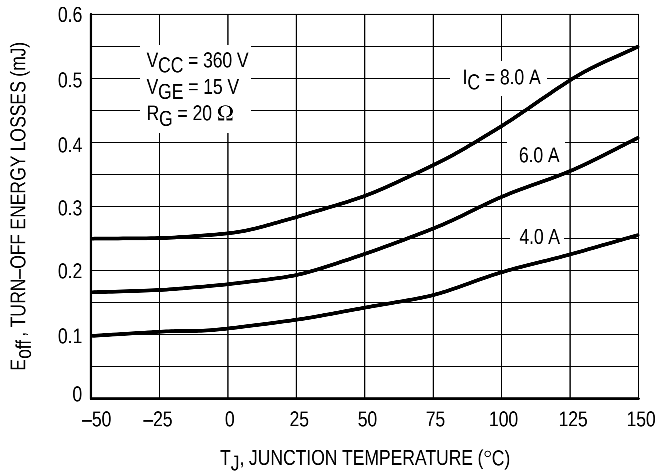


Figure 8. Turn–Off Energy Losses versus Junction Temperature

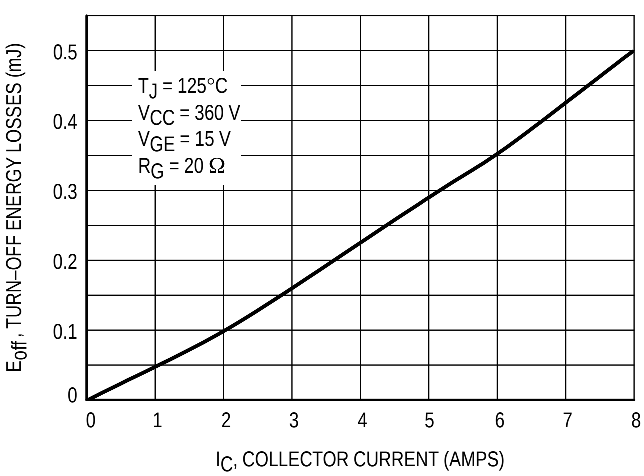


Figure 9. Turn–Off Energy Losses versus Collector Current

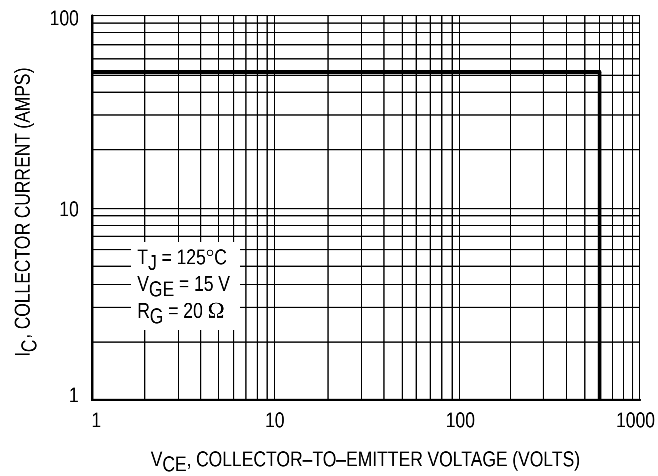
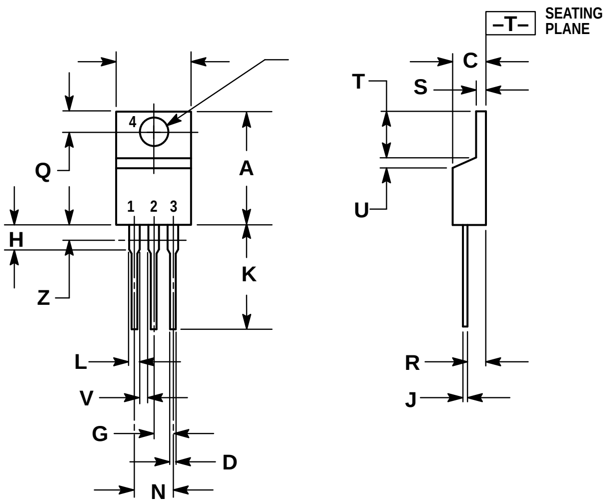


Figure 10. Reverse Biased Safe Operating Area

PACKAGE DIMENSIONS



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

STYLE 9:
PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.018	0.025	0.46	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	—	1.15	—
Z	—	0.080	—	2.04

CASE 221A–09
ISSUE Z

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